

Complementary Silicon Power Transistors

TIP3055 (NPN), TIP2955 (PNP)

Designed for general-purpose switching and amplifier applications.

Features

- DC Current Gain –

$$h_{FE} = 20-70 @ I_C$$

$$= 4.0 \text{ Adc}$$
- Collector–Emitter Saturation Voltage –

$$V_{CE(sat)} = 1.1 \text{ Vdc (Max) @ } I_C$$

$$= 4.0 \text{ Adc}$$
- Excellent Safe Operating Area
- These are Pb–Free Devices*

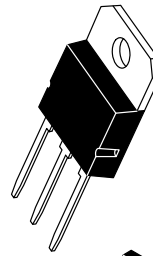
MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_{CEO}	Collector – Emitter Voltage	60	Vdc
V_{CER}	Collector – Emitter Voltage	70	Vdc
V_{CB}	Collector – Base Voltage	100	Vdc
V_{EB}	Emitter – Base Voltage	7.0	Vdc
I_C	Collector Current – Continuous	15	Adc
I_B	Base Current	7.0	Adc
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	90 0.72	W W/°C
T_J, T_{stg}	Operating and Storage Junction Temperature Range	–65 to +150	°C

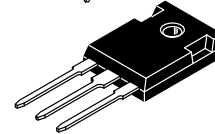
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction–to–Case	1.39	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction–to–Ambient	35.7	°C/W



SOT-93 (TO-218)
CASE 340D
STYLE 1

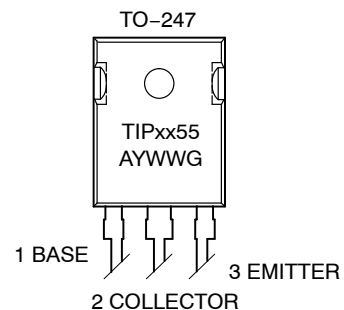
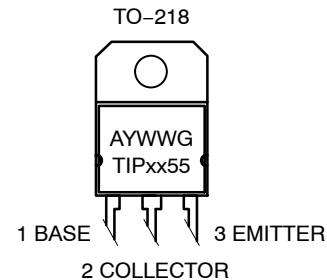


TO-247
CASE 340L
STYLE 3

NOTE: Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

15 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS, 90 WATTS

MARKING DIAGRAM



TIPxx55 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb–Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, [SOLDERM/D](#).

TIP3055 (NPN), TIP2955 (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
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OFF CHARACTERISTICS

$V_{CEO(sus)}$	Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 30\text{ mAdc}$, $I_B = 0$)	60	–	Vdc
I_{CER}	Collector Cutoff Current ($V_{CE} = 70\text{ Vdc}$, $R_{BE} = 100\text{ Ohms}$)	–	1.0	mAdc
I_{CEO}	Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$)	–	0.7	mAdc
I_{CEV}	Collector Cutoff Current ($V_{CE} = 100\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$)	–	5.0	mAdc
I_{EBO}	Emitter Cutoff Current ($V_{BE} = 7.0\text{ Vdc}$, $I_C = 0$)	–	5.0	mAdc

ON CHARACTERISTICS (Note 1)

h_{FE}	DC Current Gain ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 10\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	20 5.0	70 –	–
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage ($I_C = 4.0\text{ Adc}$, $I_B = 400\text{ mAdc}$) ($I_C = 10\text{ Adc}$, $I_B = 3.3\text{ Adc}$)	– –	1.1 3.0	Vdc
$V_{BE(on)}$	Base–Emitter On Voltage ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	–	1.8	Vdc

SECOND BREAKDOWN

$I_{S/b}$	Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 30\text{ Vdc}$, $t = 1.0\text{ s}$; Nonrepetitive)	3.0	–	Adc
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DYNAMIC CHARACTERISTICS

f_T	Current Gain — Bandwidth Product ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	2.5	–	MHz
h_{fe}	Small–Signal Current Gain ($V_{CE} = 4.0\text{ Vdc}$, $I_C = 1.0\text{ Adc}$, $f = 1.0\text{ kHz}$)	15	–	kHz

For additional design curves, refer to electrical characteristics curves of 2N3055.

1. Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TIP3055 (NPN), TIP2955 (PNP)

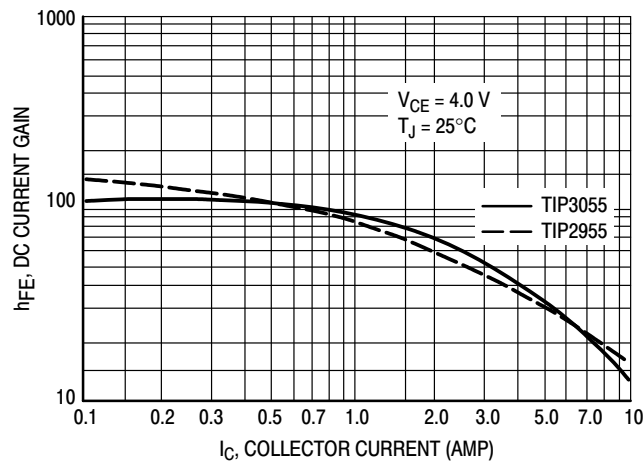


Figure 1. DC Current Gain

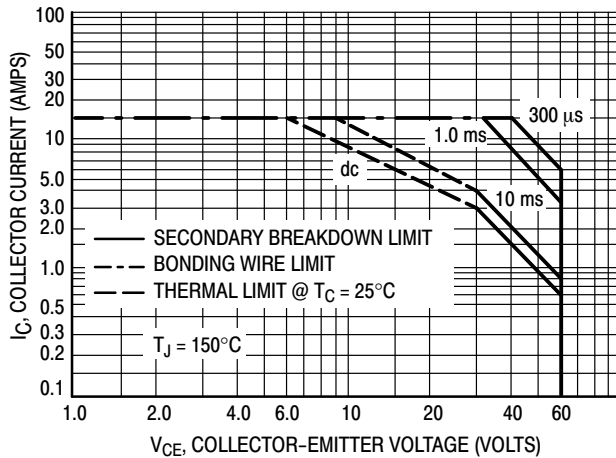


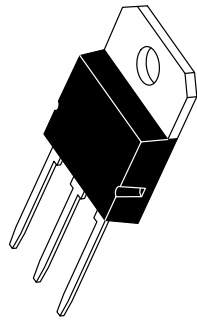
Figure 2. Maximum Rated Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature.

ORDERING INFORMATION

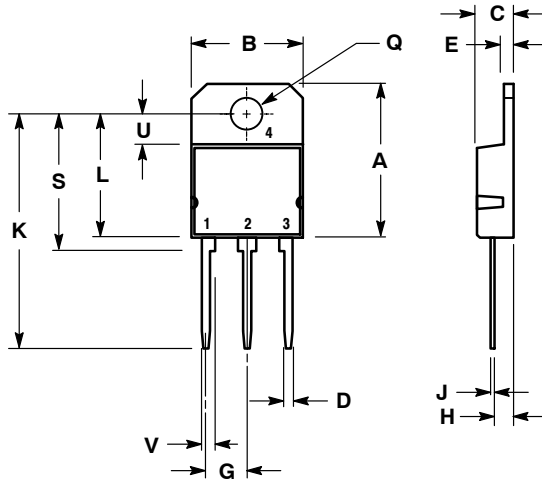
Device	Package	Shipping
TIP3055G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP2955G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP3055G	TO-247 (Pb-Free)	30 Units / Rail
TIP2955G	TO-247 (Pb-Free)	30 Units / Rail



SCALE 1:1

SOT-93 (TO-218)
CASE 340D-02
ISSUE E

DATE 03 JAN 2002



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

GENERIC
MARKING DIAGRAM*

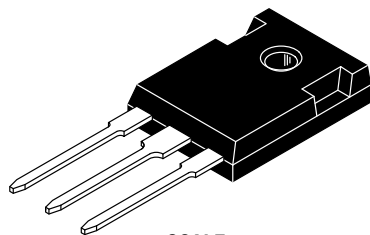


A = Assembly Location
Y = Year
WW = Work Week
XXXXX = Device Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-93 (TO-218)	PAGE 1 OF 1

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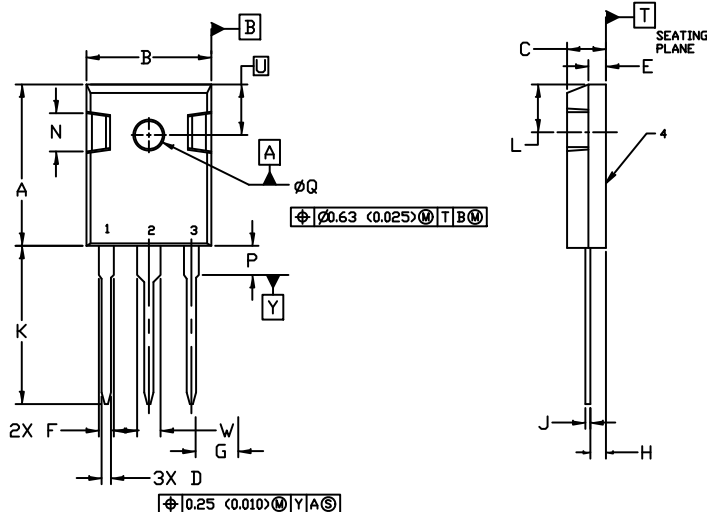
SCALE 1:1

TO-247
CASE 340L
ISSUE G

DATE 06 OCT 2021

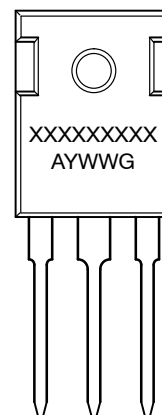
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER



	MILLIMETERS		INCHES	
DIM	MIN.	MAX.	MIN.	MAX.
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45	BSC	0.215	BSC
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	----	4.50	----	0.177
Q	3.55	3.65	0.140	0.144
U	6.15	BSC	0.242	BSC
W	2.87	3.12	0.113	0.123

GENERIC MARKING DIAGRAM*



STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 2:
PIN 1. ANODE
2. CATHODE (S)
3. ANODE 2
4. CATHODES (S)

STYLE 3:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 6:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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